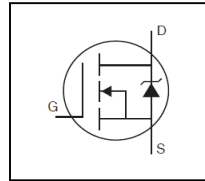


Features

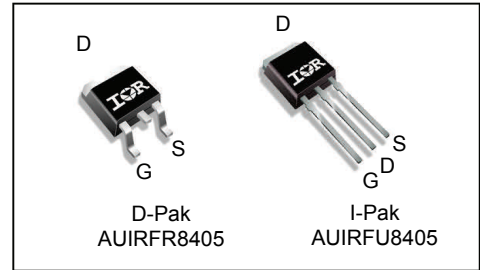
- Advanced Process Technology
- New Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



| | | |
|-------------------------|-------------|---------------|
| V_{DSS} | | 40V |
| $R_{DS(on)}$ | typ. | 1.65mΩ |
| | max. | 1.98mΩ |
| I_D (Silicon Limited) | | 211A Ⓞ |
| I_D (Package Limited) | | 100A |

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and wide variety of other applications.



Applications

- Electric Power Steering (EPS)
- Battery Switch
- Start/Stop Micro Hybrid
- Heavy Loads
- DC-DC Converter

| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

| Base part number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|--------------|--------------------|----------|-----------------------|
| | | Form | Quantity | |
| AUIRFU8405 | I-Pak | Tube | 75 | AUIRFU8405 |
| AUIRFR8405 | D-Pak | Tube | 75 | AUIRFR8405 |
| | | Tape and Reel Left | 3000 | AUIRFR8405TRL |

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

| Symbol | Parameter | Max. | Units |
|---------------------------|------------------------------------------------------------|--------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) | 211Ⓞ | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) | 150Ⓞ | |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited) | 100 | |
| I_{DM} | Pulsed Drain Current ② | 804Ⓞ | |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 163 | W |
| | Linear Derating Factor | 1.1 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| T_J | Operating Junction and | -55 to + 175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds (1.6mm from case) | 300 | |

Avalanche Characteristics

| | | | |
|-------------------|-----------------------------------------------------|---------------------------|----|
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ③ | 208 | mJ |
| $E_{AS} (tested)$ | Single Pulse Avalanche Energy (Tested Limited) ③ | 256 | |
| I_{AR} | Avalanche Current ② | See Fig. 14, 15, 24a, 24b | A |
| E_{AR} | Repetitive Avalanche Energy ② | | mJ |

Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|------------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ④ | — | 0.92 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount) ④ | — | 50 | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 110 | |

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*Qualification standards can be found at www.infineon.com

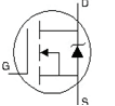
Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------------------------------------|--------------------------------------|------|------|------|-------|---------------------------------------------------------------------|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 40 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.03 | — | V/°C | Reference to 25°C, I _D = 5mA ② |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 1.65 | 1.98 | mΩ | V _{GS} = 10V, I _D = 90A** ⑤ |
| V _{GS(th)} | Gate Threshold Voltage | 2.2 | 3.0 | 3.9 | V | V _{DS} = V _{GS} , I _D = 100μA |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 40V, V _{GS} = 0V |
| | | — | — | 150 | | V _{DS} = 40V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |
| R _G | Internal Gate Resistance | — | 2.3 | — | Ω | |

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

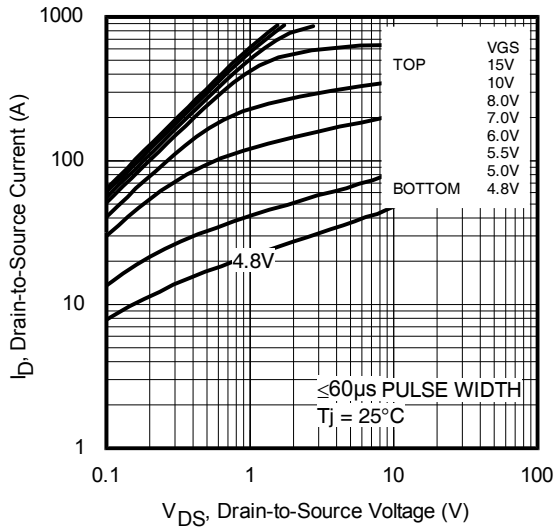
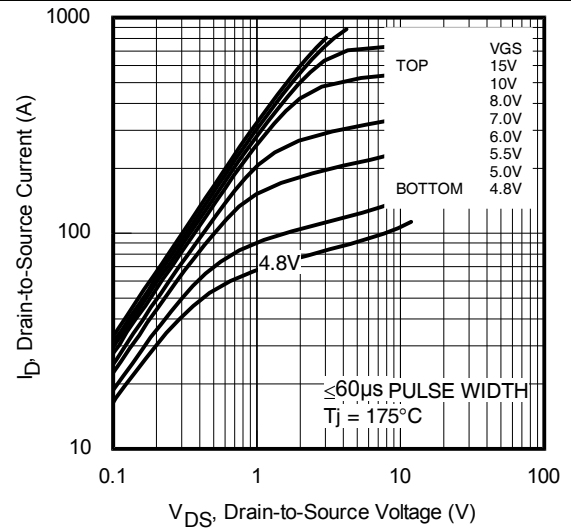
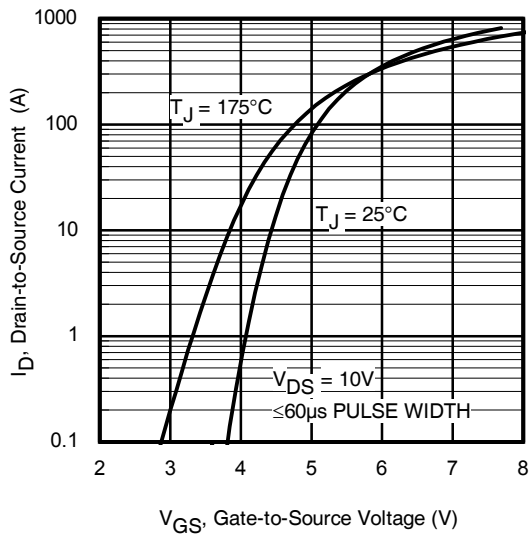
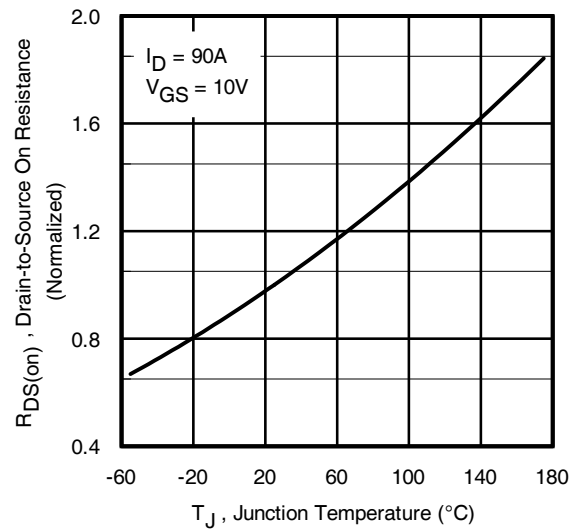
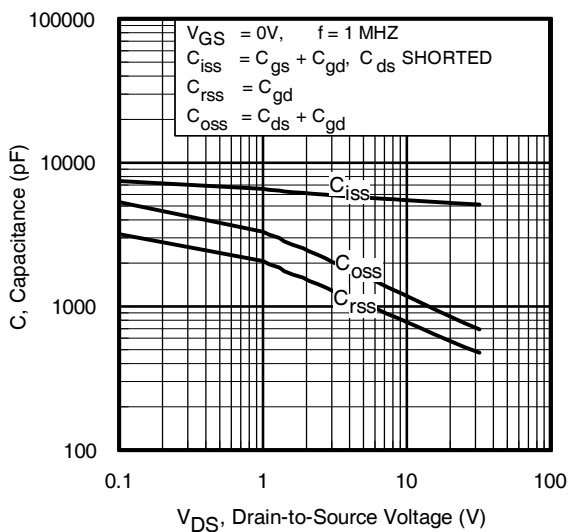
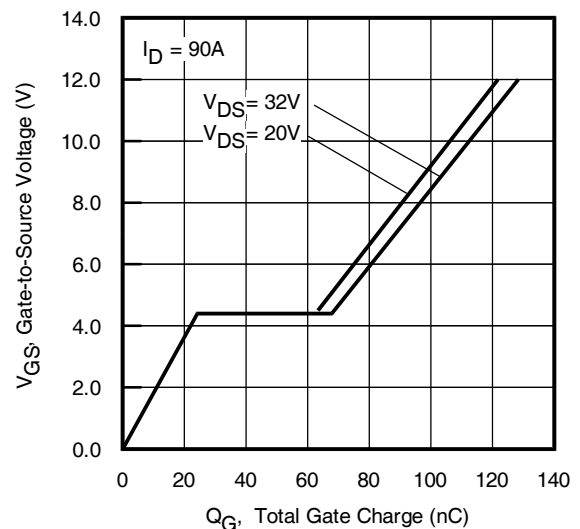
| | | | | | | |
|----------------------------|-------------------------------------------------------------|-----|------|-----|----|-----------------------------------------------------|
| g _{fs} | Forward Trans conductance | 294 | — | — | S | V _{DS} = 10V, I _D = 90A** |
| Q _g | Total Gate Charge | — | 103 | 155 | nC | I _D = 90A** |
| Q _{gs} | Gate-to-Source Charge | — | 26 | — | | V _{DS} = 20V |
| Q _{gd} | Gate-to-Drain Charge | — | 38 | — | | V _{GS} = 10V ⑤ |
| Q _{sync} | Total Gate Charge Sync. (Q _g - Q _{gd}) | — | 65 | — | | |
| t _{d(on)} | Turn-On Delay Time | — | 12 | — | ns | V _{DD} = 26V |
| t _r | Rise Time | — | 80 | — | | I _D = 90A** |
| t _{d(off)} | Turn-Off Delay Time | — | 51 | — | | R _G = 2.7Ω |
| t _f | Fall Time | — | 51 | — | | V _{GS} = 10V ⑤ |
| C _{iss} | Input Capacitance | — | 5171 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 770 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 523 | — | | f = 1.0MHz, See Fig. 5 |
| C _{oss eff. (ER)} | Effective Output Capacitance (Energy Related) | — | 939 | — | | V _{GS} = 0V, V _{DS} = 0V to 32V ⑦ |
| C _{oss eff. (TR)} | Effective Output Capacitance (Time Related) | — | 1054 | — | | V _{GS} = 0V, V _{DS} = 0V to 32V ⑥ |

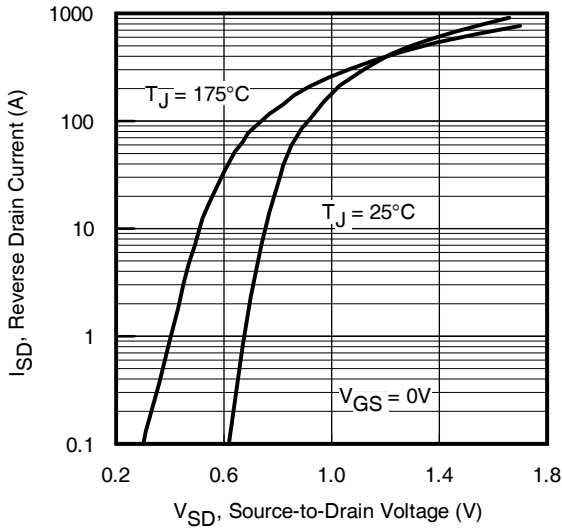
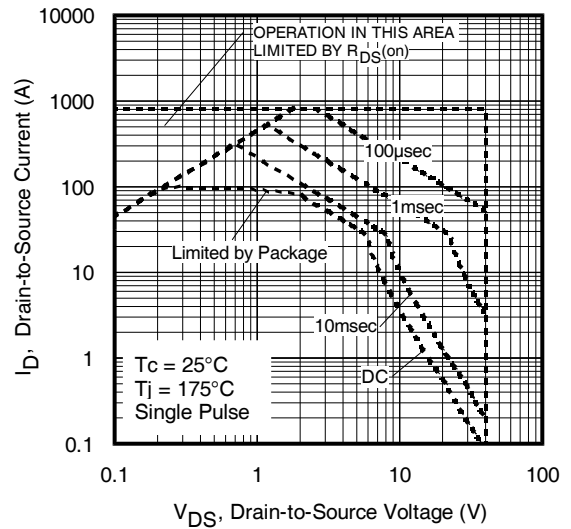
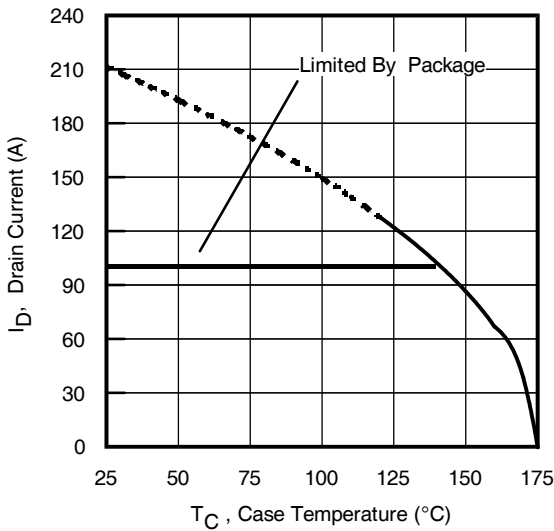
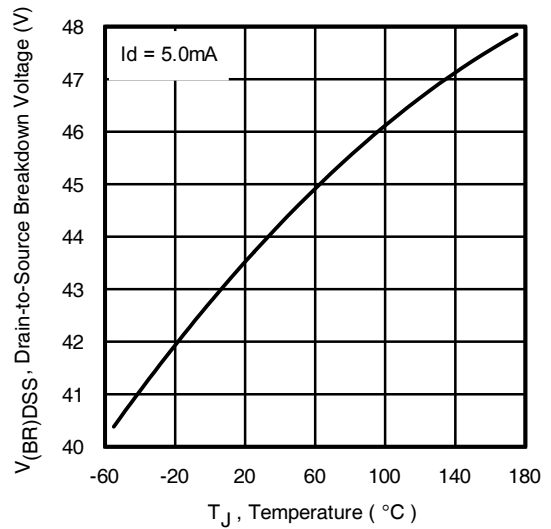
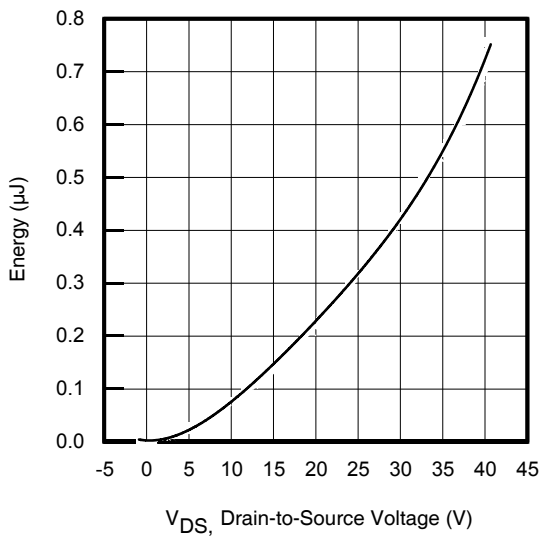
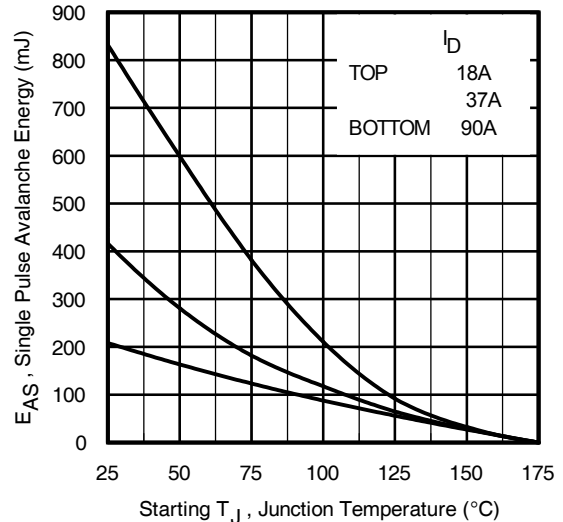
Diode Characteristics

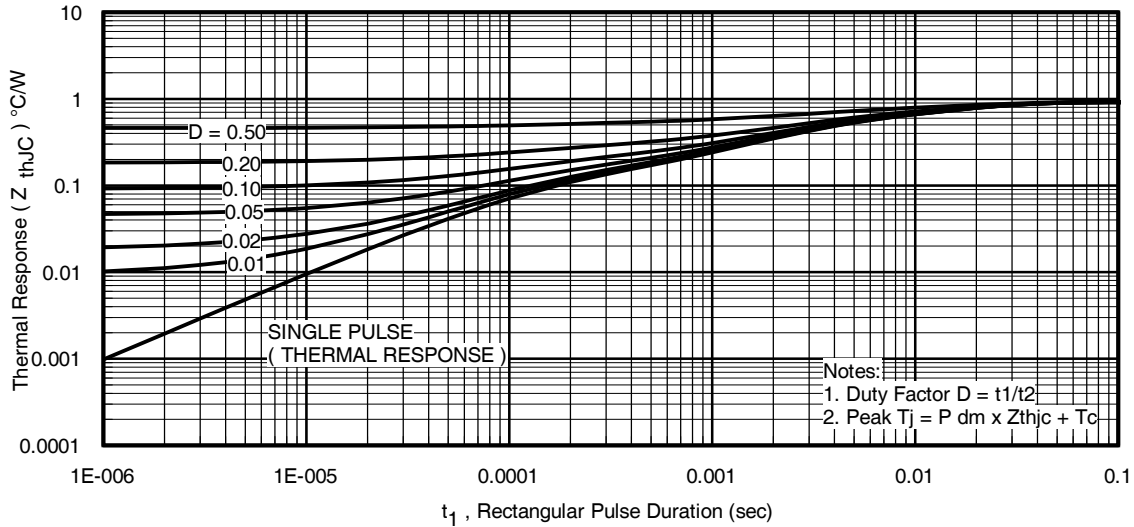
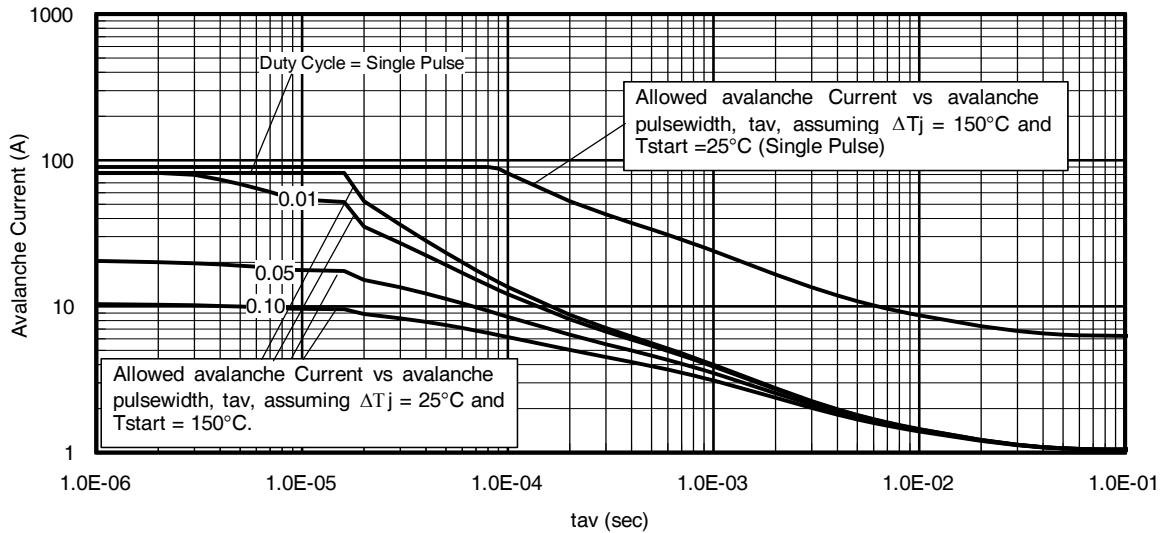
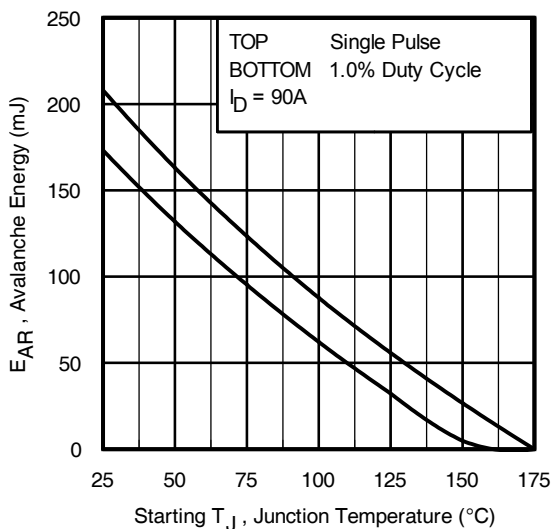
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------|----------------------------------------|------|------|------|-------|------------------------------------------------------------------------------------------------------------------------------------------------------|
| I _S | Continuous Source Current (Body Diode) | — | — | 211① | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 804⑩ | | |
| V _{SD} | Diode Forward Voltage | — | 0.9 | 1.3 | V | T _J = 25°C, I _S = 90A**, V _{GS} = 0V ⑤ |
| dv/dt | Peak Diode Recovery dv/dt④ | — | 2.1 | — | V/ns | T _J = 175°C, I _S = 90A**, V _{DS} = 40V |
| t _{rr} | Reverse Recovery Time | — | 28 | — | ns | T _J = 25°C |
| | | — | 29 | — | | T _J = 125°C |
| Q _{rr} | Reverse Recovery Charge | — | 19 | — | nC | T _J = 25°C |
| | | — | 20 | — | | T _J = 125°C |
| I _{RRM} | Reverse Recovery Current | — | 1.1 | — | A | T _J = 25°C |

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 100A by source bonding technology. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
 - ② Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
 - ③ Limited by T_{Jmax}, starting T_J = 25°C, L = 0.051mH, R_G = 50Ω, I_{AS} = 90A, V_{GS} = 10V. Part not recommended for use above this value.
 - ④ I_{SD} ≤ 90A, di/dt ≤ 1304A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
 - ⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.
 - ⑥ C_{oss eff. (TR)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
 - ⑦ C_{oss eff. (ER)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
 - ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
 - ⑨ R_θ is measured at T_J approximately 90°C.
 - ⑩ Pulse drain current is limited by source bonding technology.
- ** All AC and DC test condition based on old Package limitation current = 90A.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig. 9 Maximum Drain Current vs. Case Temperature

Fig 10. Drain-to-Source Breakdown Voltage

Fig. 11 Typical Coss Stored Energy

Fig 12. Maximum Avalanche Energy vs. Drain Current

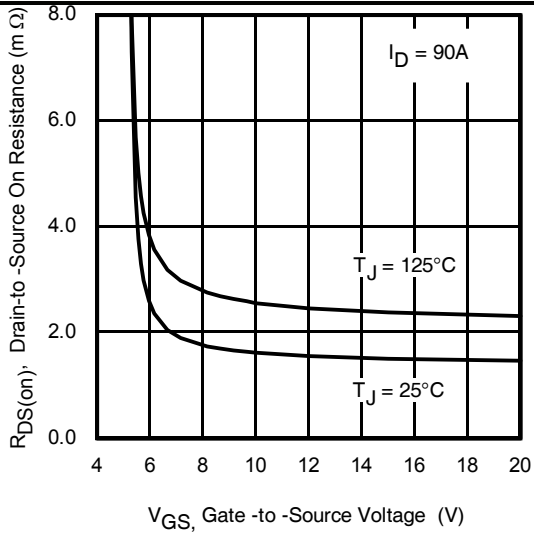
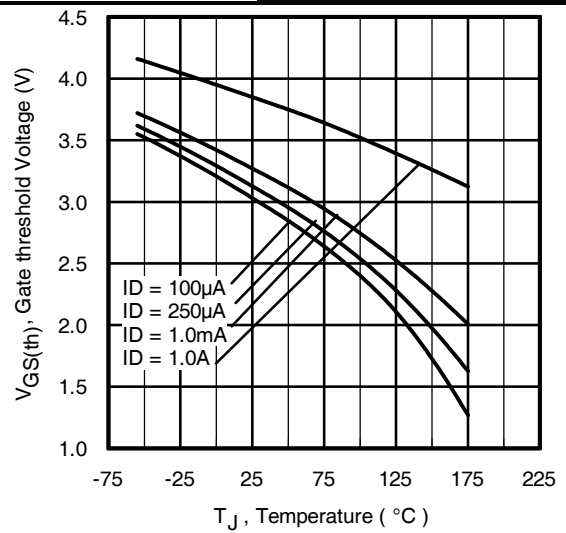
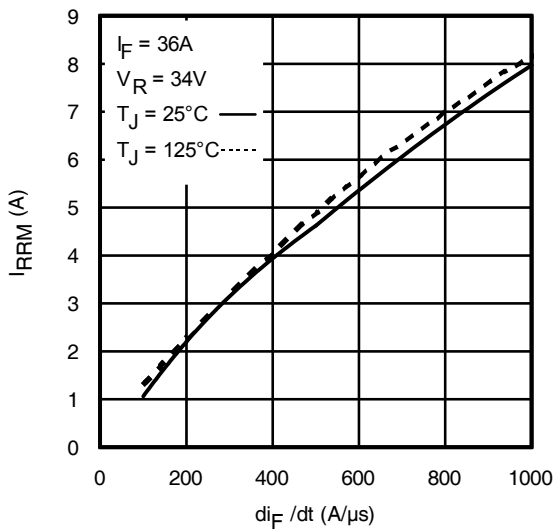
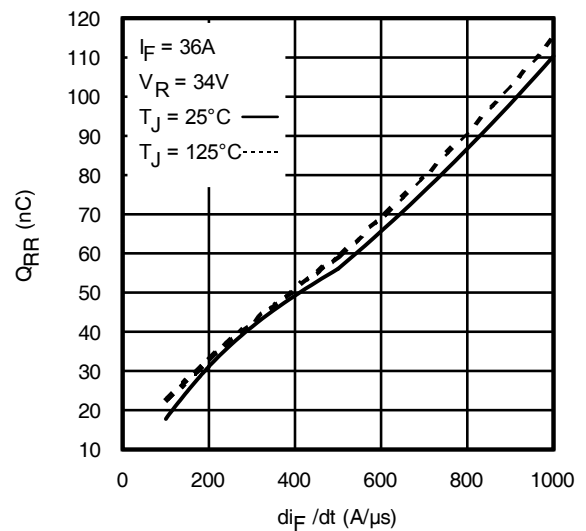
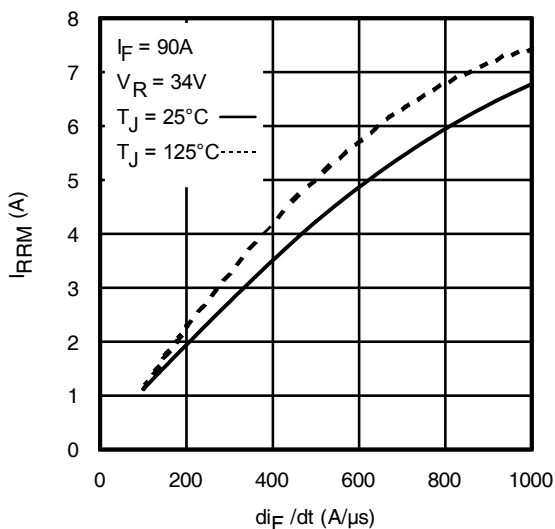
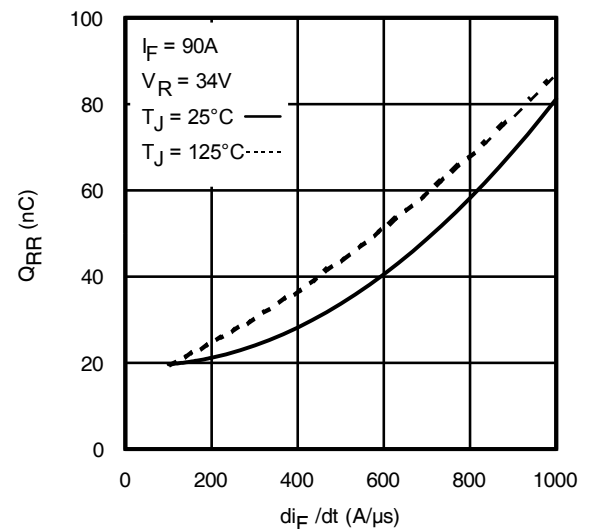

Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 14. Typical Avalanche Current Vs. Pulse width

Fig 15. Maximum Avalanche Energy Vs. Temperature
**Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.infineon.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 13, 14).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$


Fig. 16. On-Resistance vs. Gate Voltage

Fig. 17 - Threshold Voltage vs. Temperature

Fig. 18 - Typical Recovery Current vs. di/dt

Fig. 19 - Typical Stored Charge vs. di/dt

Fig. 20 - Typical Recovery Current vs. di/dt

Fig. 21 - Typical Stored Charge vs. di/dt

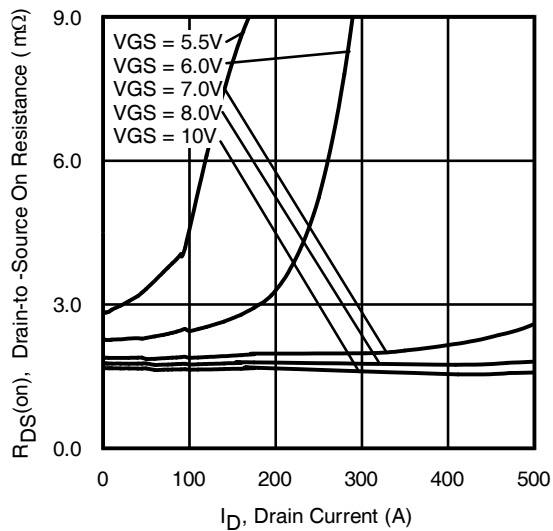
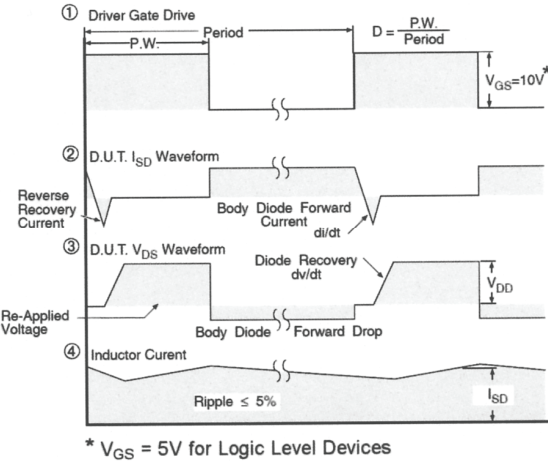
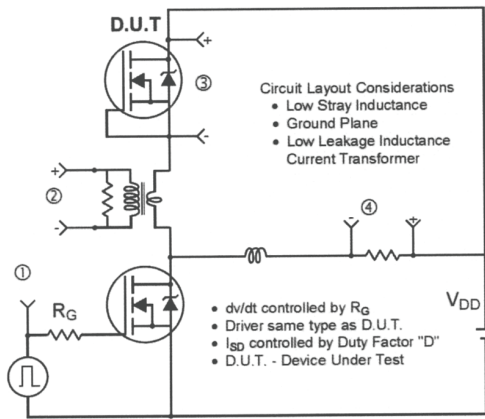
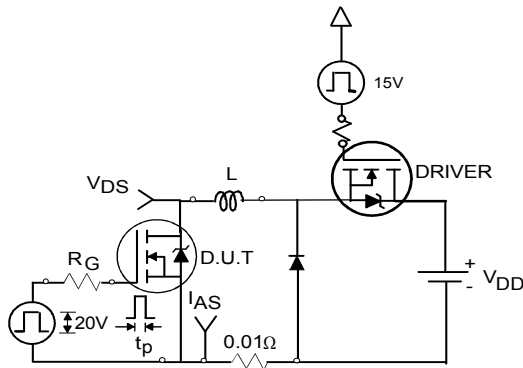
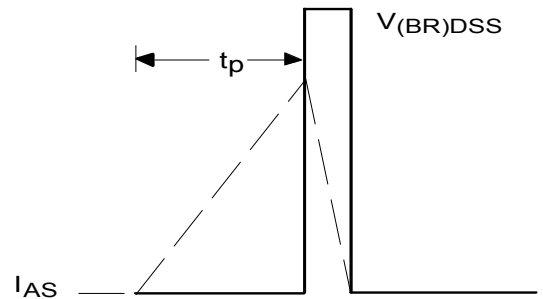
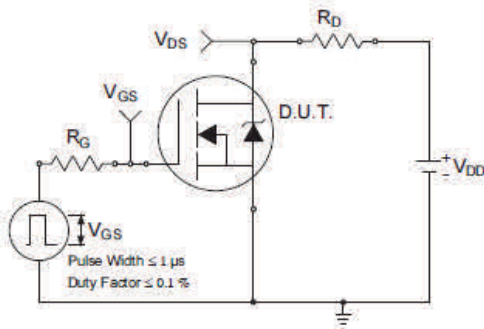
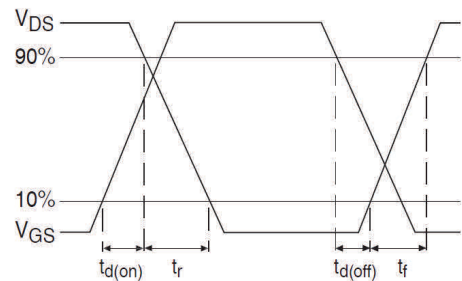
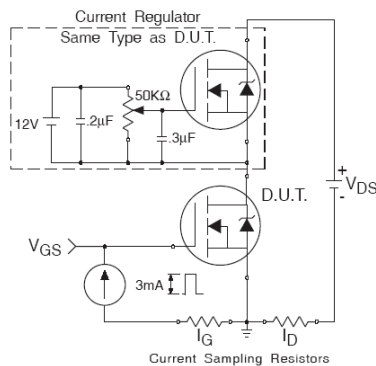
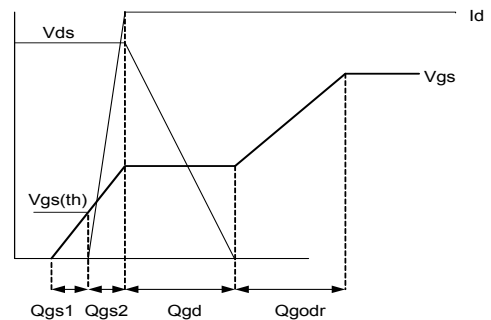


Fig 22. Typical On-Resistance vs. Drain Current


Fig 23. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

Fig 24a. Unclamped Inductive Test Circuit

Fig 24b. Unclamped Inductive Waveforms

Fig 25a. Switching Time Test Circuit

Fig 25b. Switching Time Waveforms

Fig 26a. Gate Charge Test Circuit

Fig 26b. Gate Charge Waveform

D-Pak (TO-252AA) Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

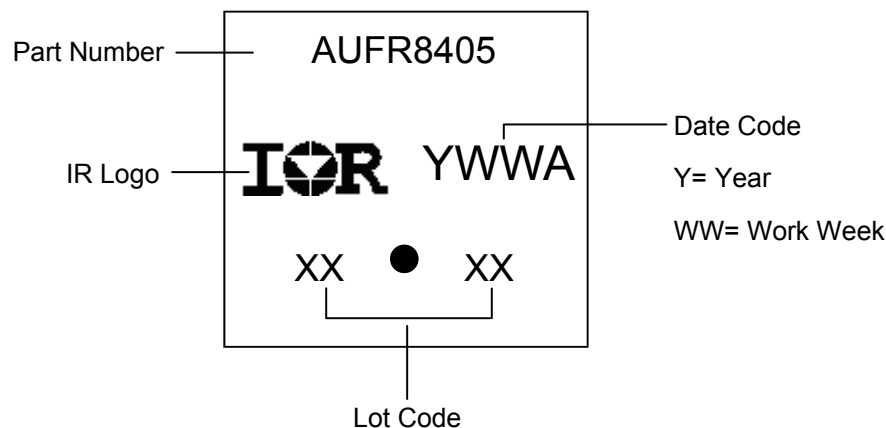
| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|-----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | .086 | .094 | |
| A1 | — | 0.13 | — | .005 | |
| b | 0.64 | 0.89 | .025 | .035 | |
| b1 | 0.65 | 0.79 | .025 | .031 | 7 |
| b2 | 0.76 | 1.14 | .030 | .045 | |
| b3 | 4.95 | 5.46 | .195 | .215 | 4 |
| c | 0.46 | 0.61 | .018 | .024 | |
| c1 | 0.41 | 0.56 | .016 | .022 | 7 |
| c2 | 0.46 | 0.89 | .018 | .035 | |
| D | 5.97 | 6.22 | .235 | .245 | 6 |
| D1 | 5.21 | — | .205 | — | 4 |
| E | 6.35 | 6.73 | .250 | .265 | 6 |
| E1 | 4.32 | — | .170 | — | 4 |
| e | 2.29 BSC | | .090 BSC | | |
| H | 9.40 | 10.41 | .370 | .410 | |
| L | 1.40 | 1.78 | .055 | .070 | |
| L1 | 2.74 BSC | | .108 REF. | | |
| L2 | 0.51 BSC | | .020 BSC | | |
| L3 | 0.89 | 1.27 | .035 | .050 | 4 |
| L4 | — | 1.02 | — | .040 | |
| L5 | 1.14 | 1.52 | .045 | .060 | 3 |
| φ | 0" | 10" | 0" | 10" | |
| φ1 | 0" | 15" | 0" | 15" | |
| φ2 | 25" | 35" | 25" | 35" | |

LEAD ASSIGNMENTS
HEXFET

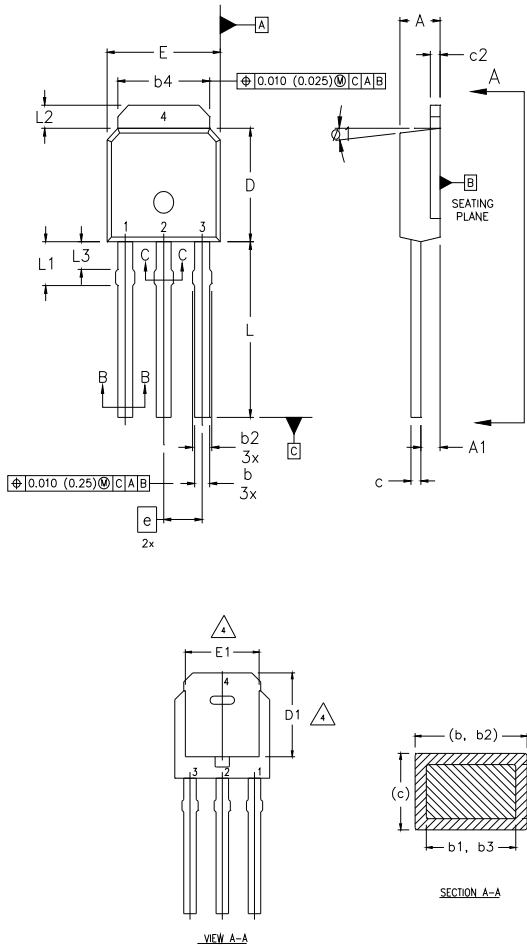
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

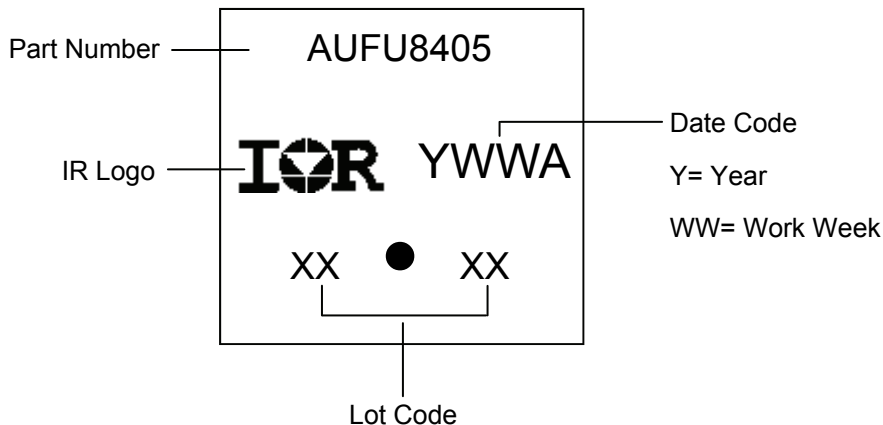
I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

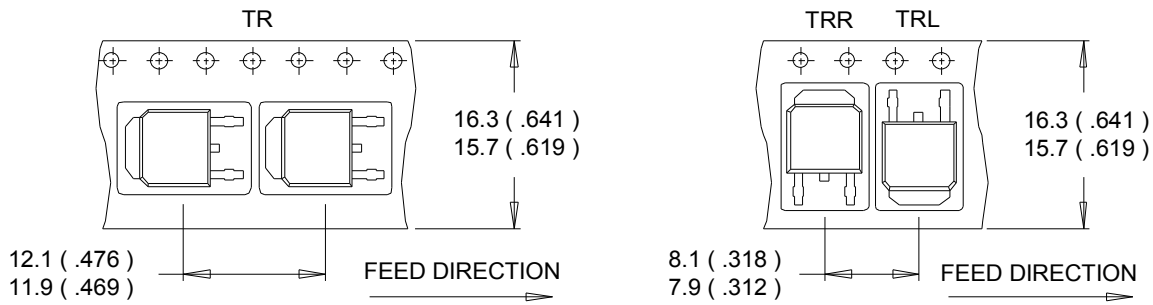
LEAD ASSIGNMENTS

- HEXFET**
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

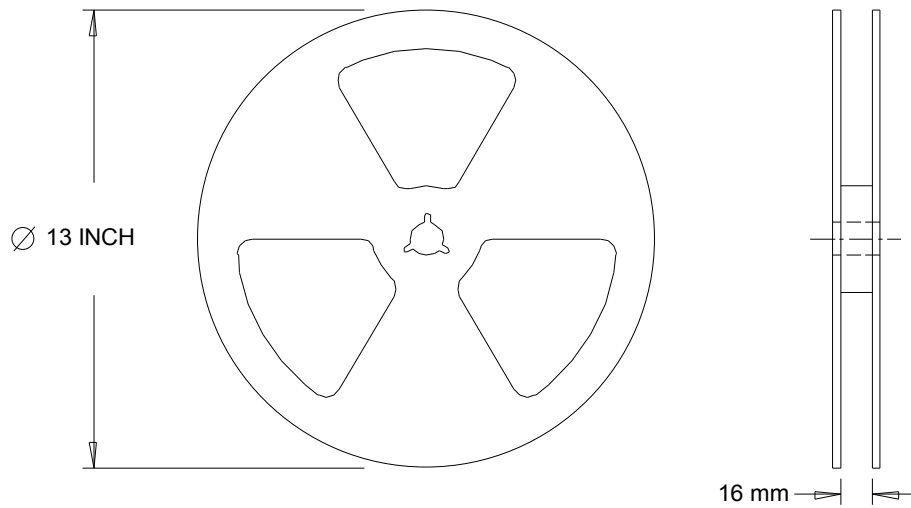
| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|------|-----------|-------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | 0.086 | .094 | |
| A1 | 0.89 | 1.14 | 0.035 | 0.045 | |
| b | 0.64 | 0.89 | 0.025 | 0.035 | |
| b1 | 0.64 | 0.79 | 0.025 | 0.031 | 4 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | |
| b3 | 0.76 | 1.04 | 0.030 | 0.041 | |
| b4 | 5.00 | 5.46 | 0.195 | 0.215 | 4 |
| c | 0.46 | 0.61 | 0.018 | 0.024 | |
| c1 | 0.41 | 0.56 | 0.016 | 0.022 | |
| c2 | .046 | 0.86 | 0.018 | 0.035 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | 3, 4 |
| D1 | 5.21 | - | 0.205 | - | 4 |
| E | 6.35 | 6.73 | 0.250 | 0.265 | 3, 4 |
| E1 | 4.32 | - | 0.170 | - | 4 |
| e | 2.29 | | 0.090 BSC | | |
| L | 8.89 | 9.60 | 0.350 | 0.380 | |
| L1 | 1.91 | 2.29 | 0.075 | 0.090 | |
| L2 | 0.89 | 1.27 | 0.035 | 0.050 | 4 |
| L3 | 1.14 | 1.52 | 0.045 | 0.060 | 5 |
| ø1 | 0" | 15" | 0" | 15" | |

I-Pak (TO-251AA) Part Marking Information


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D-Pak (TO-252AA) Tape & Reel Information (Dimensions are shown in millimeters (inches))

NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.


NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information

| | | | |
|-----------------------------------|----------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|
| Qualification Level | | Automotive (per AEC-Q101) | |
| | | Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | D-Pak | MSL1 |
| | | I-Pak | |
| ESD | Machine Model | Class M3 (+/- 400V) [†] AEC-Q101-002 | |
| | Human Body Model | Class H1C (+/- 2000V) [†] AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- 2000V) [†] AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

† Highest passing voltage.

Revision History

| Date | Comments |
|------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|
| 10/17/2014 | <ul style="list-style-type: none"> Corrected label on SOA curve Fig 8 on page 4. Updated Package outline on page 9 & 10 |
| 10/12/2015 | <ul style="list-style-type: none"> Updated datasheet with corporate template Corrected ordering table on page 1. |

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